

SOT23 PNP SILICON PLANAR MEDIUM POWER TRANSISTOR

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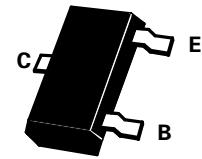
FEATURES

Low equivalent on resistance $R_{CE(sat)} = 350\text{m}\Omega$ at 1A

PART MARKING DETAIL - 91A

COMPLEMENTARY TYPE - FMMT491A

FMMT591A



ABSOLUTE MAXIMUM RATINGS.

| PARAMETER | SYMBOL | VALUE | UNIT |
|---|---------------|-------------|------|
| Collector-Base Voltage | V_{CBO} | -40 | V |
| Collector-Emitter Voltage | V_{CEO} | -40 | V |
| Emitter-Base Voltage | V_{EBO} | -5 | V |
| Peak Pulse Current | I_{CM} | -2 | A |
| Continuous Collector Current | I_C | -1 | A |
| Base Current | I_B | -200 | mA |
| Power Dissipation at $T_{amb}=25^\circ\text{C}$ | P_{tot} | 500 | mW |
| Operating and Storage Temperature Range | $T_j:T_{stg}$ | -55 to +150 | °C |

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$).

| PARAMETER | SYMBOL | MIN. | MAX. | UNIT | CONDITIONS. |
|---------------------------------------|---------------|--------------------------------|-----------------------|-------------|--|
| Collector-Base Breakdown Voltage | $V_{(BR)CBO}$ | -40 | | V | $I_C=-100\mu\text{A}$ |
| Collector-Emitter Breakdown Voltage | $V_{(BR)CEO}$ | -40 | | V | $I_C=-10\text{mA}^*$ |
| Emitter-Base Breakdown Voltage | $V_{(BR)EBO}$ | -5 | | V | $I_E=-100\mu\text{A}$ |
| Collector Cut-Off Current | I_{CBO} | | -100 | nA | $V_{CB}=-30\text{V}$ |
| Emitter Cut-Off Current | I_{EBO} | | -100 | nA | $V_{EB}=-4\text{V}$ |
| Collector-Emitter Cut-Off Current | I_{CES} | | -100 | nA | $V_{CES}=-30\text{V}$ |
| Collector-Emitter Saturation Voltage | $V_{CE(sat)}$ | | -0.2 -0.35 -0.5 | V V V | $I_C=-100\text{mA}, I_B=-1\text{mA}^*$ $I_C=-500\text{mA}, I_B=-20\text{mA}^*$ $I_C=-1\text{A}, I_B=-100\text{mA}^*$ |
| Base-Emitter Saturation Voltage | $V_{BE(sat)}$ | | -1.1 | V | $I_C=-1\text{A}, I_B=-50\text{mA}^*$ |
| Base-Emitter Turn-on Voltage | $V_{BE(on)}$ | | -1.0 | V | $I_C=-1\text{A}, V_{CE}=-5\text{V}^*$ |
| Static Forward Current Transfer Ratio | h_{FE} | 300 300 250 160 30 | 800 | | $I_C=1\text{mA},$ $I_C=100\text{mA}^*,$ $I_C=500\text{mA}^*, V_{CE}=-5\text{V}$ $I_C=1\text{A}^*,$ $I_C=2\text{A}^*$ |
| Transition Frequency | f_T | 150 | | MHz | $I_C=50\text{mA}, V_{CE}=-10\text{V}$ $f=100\text{MHz}$ |
| Output Capacitance | C_{obo} | | 10 | pF | $V_{CB}=-10\text{V}, f=1\text{MHz}$ |

*Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤ 2%

Spice parameter data is available upon request for this device

FMMT591A

TYPICAL CHARACTERISTICS

